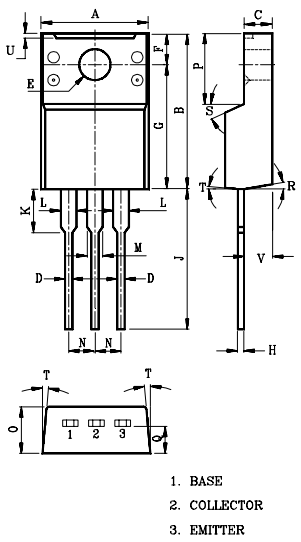
KTB1424

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE DARLINGTON TRANSISTOR.

FEATURES

- High DC Current Gain : h_{FE}=3000(Min.) (V_{CE}=-2V, I_C=-1A)
- Complementary to KTD2424.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	2.70±0.30
D	0.85 MAX
E	ø3.20±0.20
F	3.00±0.30
G	12.30 MAX
H	0.75 MAX
J	13.60±0.50
K	3.90 MAX
L	1.20
M	1.30
N	2.54
O	4.50±0.20
P	6.80
Q	2.60±0.20
R	10°
S	25°
T	5°
U	0.5
V	2.60±0.15

1. BASE
2. COLLECTOR
3. EMITTER

TO-220IS

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-3	A
Base Current	I_B	-0.5	A
Collector Power Dissipation (Tc=25℃)	P_C	25	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=-80V, I_E=0	-	-	-20	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=-10V, I_C=0	-	-	-100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-60	-	-	V
DC Current Gain		$h_{FE}(1)$	V_{CE}=-2V, I_C=-1A	3000	-	-	
		$h_{FE}(2)$	V_{CE}=-2V, I_C=-3A	1000	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C=-3A, I_B=-30mA	-	-	-1.5	V
	Base-Emitter	$V_{BE(sat)}$	I_C=-3A, I_B=-30mA	-	-	-2.8	